

## 4AE11

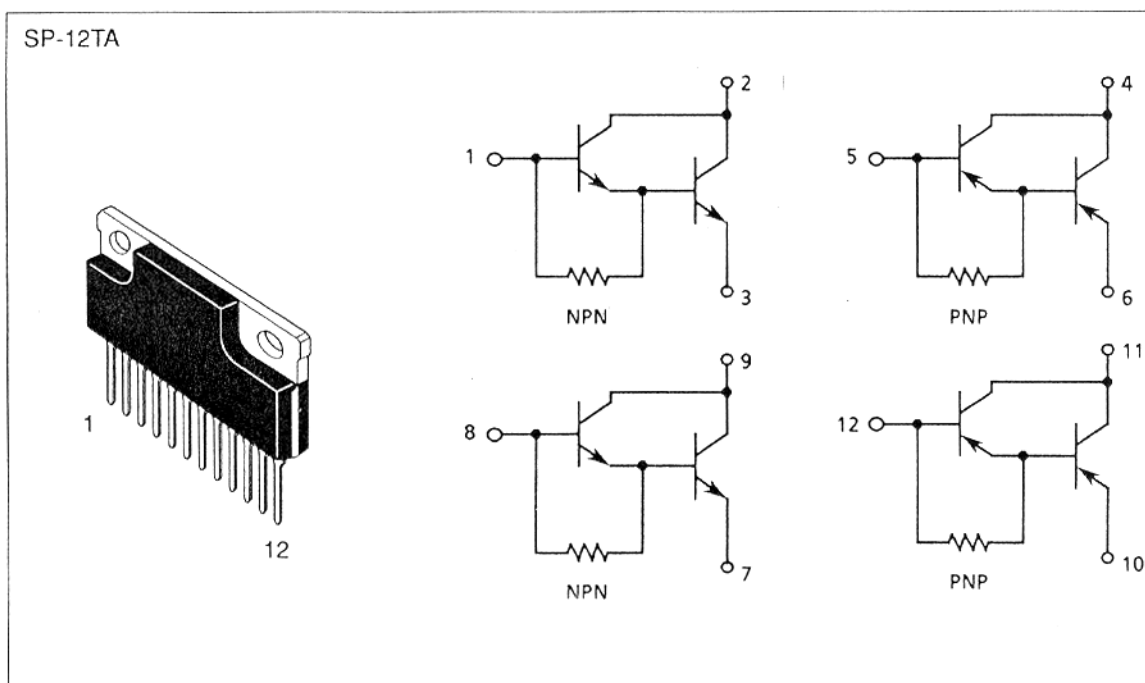
Silicon NPN/PNP Triple Diffused  
Low Frequency Power Amplifier

### Absolute Maximum Ratings

(for each device,  $T_a = 25^\circ\text{C}$ )

Item	Symbol	Rating		Unit
		NPN	PNP	
Collector to base voltage	$V_{CBO}$	300	-300	V
Collector to emitter voltage	$V_{CEO}$	300	-300	V
Emitter to base voltage	$V_{EBO}$	7	-7	V
Collector current	$I_C$	0.3	-0.3	A
Collector peak current	$i_{C(\text{peak})}$	0.6	-0.6	A
Collector power dissipation	$P_C^1$	32	32	W
Junction temperature	$T_j$	150	150	$^\circ\text{C}$
Storage temperature	$T_{\text{stg}}$	-55 to 150	-55 to 150	$^\circ\text{C}$

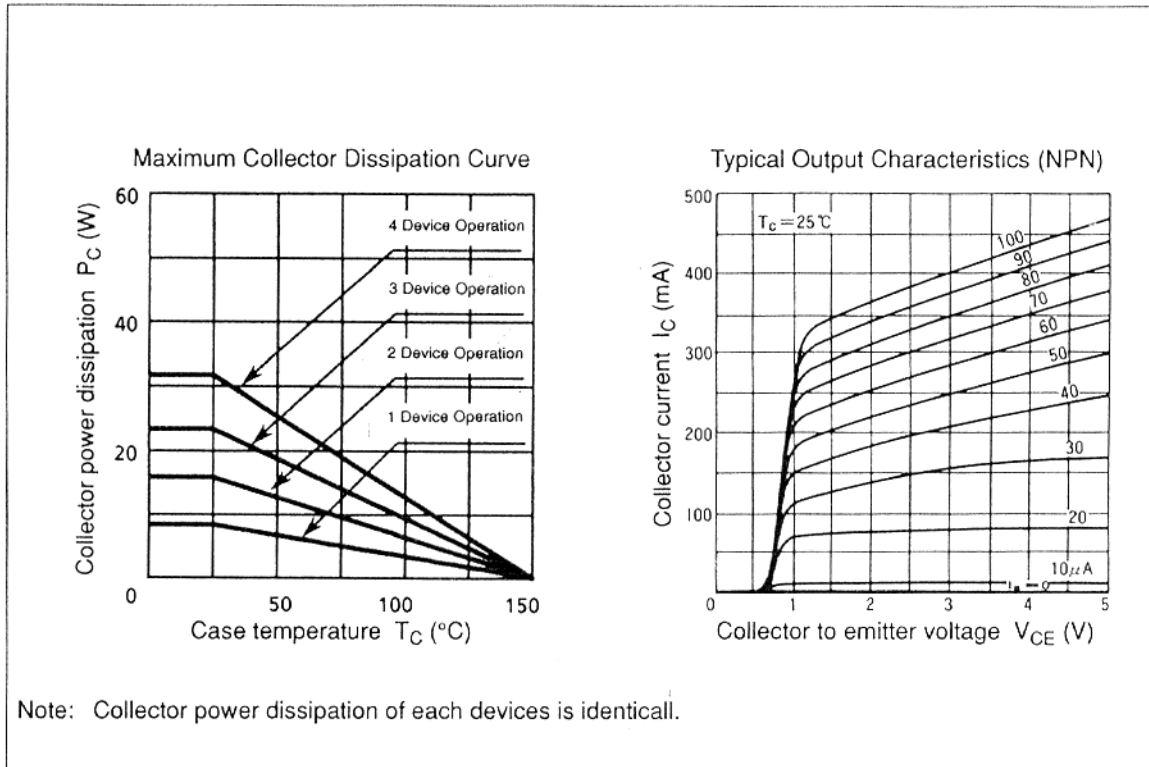
Note: 1. Value at  $T_C = 25^\circ\text{C}$ .



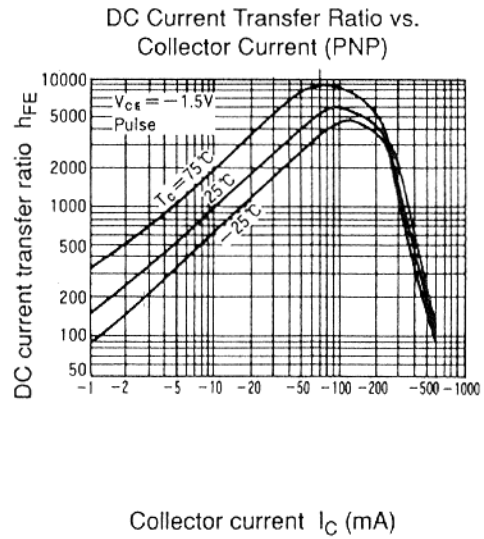
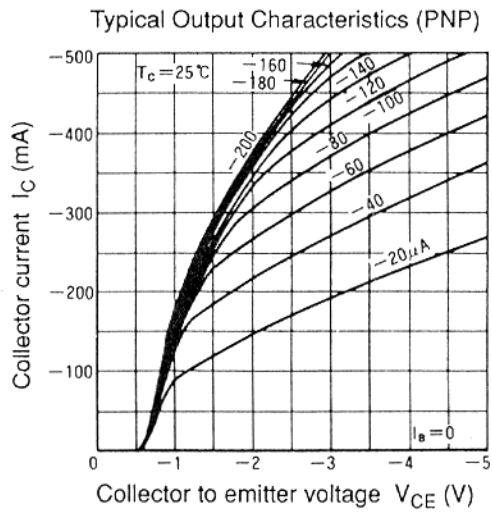
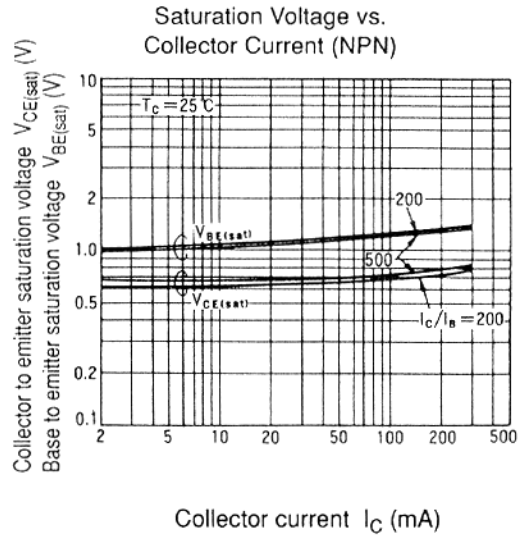
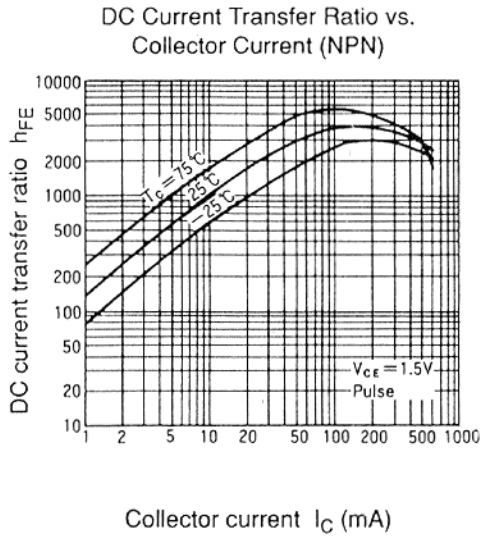
### Electrical Characteristics (Ta = 25°C)

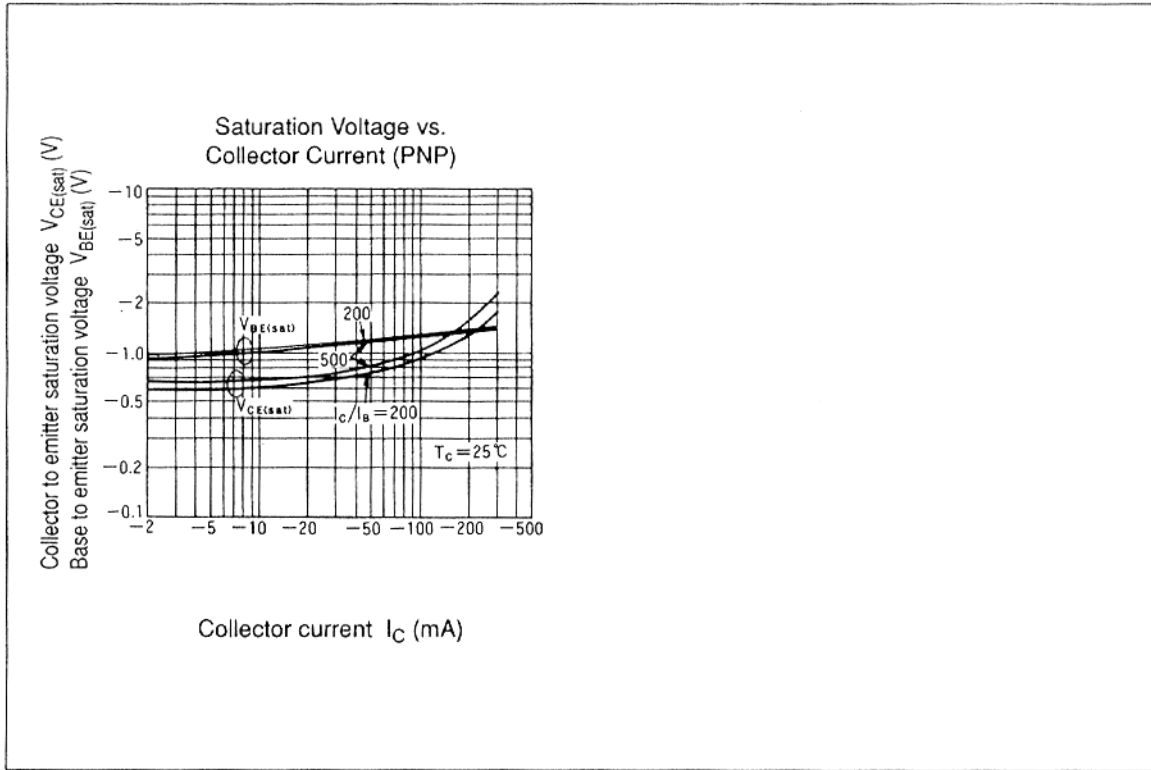
Item	Symbol	Min	Typ	Max	Unit	Test condition
Collector to base breakdown voltage	$V_{(BR)CBO}$	300	—	—	V	$I_C = 1 \text{ mA}, I_E = 0$
Collector to emitter breakdown voltage	$V_{(BR)CEO}$	300	—	—	V	$I_C = 10 \text{ mA}, R_{BE} = \infty$
Emitter to base breakdown voltage	$V_{(BR)EBO}$	7	—	—	V	$I_E = 1 \text{ mA}, I_C = 0$
Collector cutoff current	$I_{CBO}$	—	—	10	$\mu\text{A}$	$V_{CB} = 300 \text{ V}, I_E = 0$
	$I_{CEO}$	—	—	10		$V_{CE} = 60 \text{ V}, R_{BE} = \infty$
Emitter cutoff current	$I_{EBO}$	—	—	10	$\mu\text{A}$	$V_{EB} = 5 \text{ V}, I_C = 0$
DC current transfer ratio	$h_{FE1}$	1000	—	—		$V_{CE} = 1.5 \text{ V}, I_C = 20 \text{ mA}^{*1}$
	$h_{FE2}$	3000	—	30000		$V_{CE} = 1.5 \text{ V}, I_C = 100 \text{ mA}^{*1}$
Collector to emitter saturation voltage	$V_{CE(sat)}$	—	—	1.5	V	$I_C = 100 \text{ mA}, I_B = 0.2 \text{ mA}^{*1}$
Base to emitter saturation voltage	$V_{BE(sat)}$	—	—	2.0	V	$I_C = 100 \text{ mA}, I_B = 0.2 \text{ mA}^{*1}$

Note: 1. Pulse Test.  
2. The minus sign of PNP is omitted.

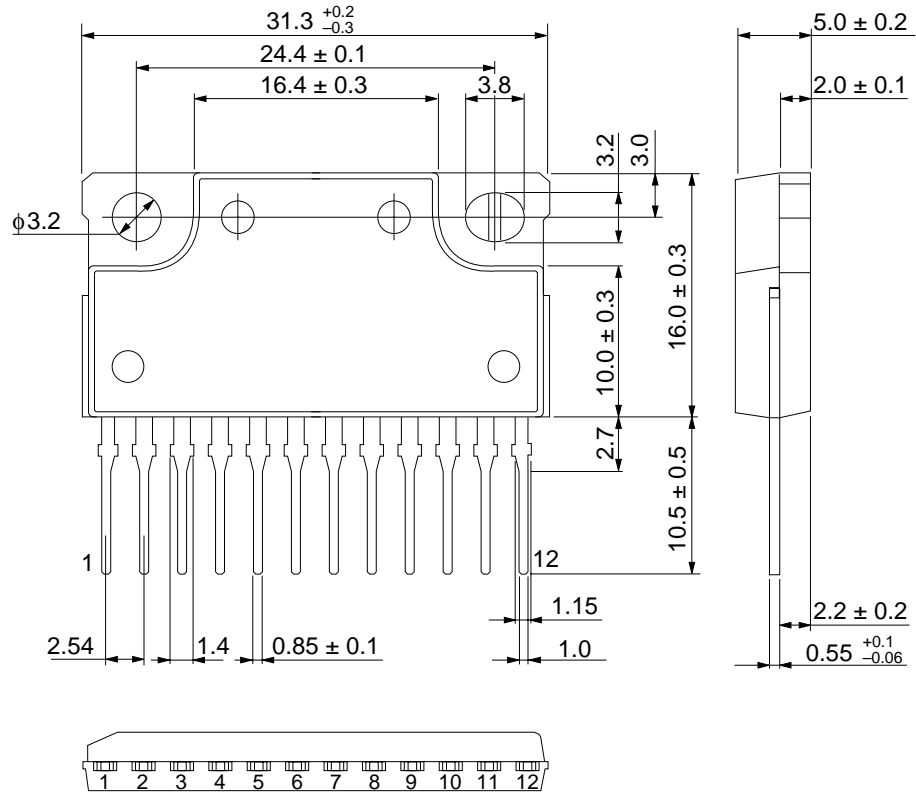


## 4AE11





Unit: mm



Pin No.	1	2	3	4	5	6	7	8	9	10	11	12
Electrode	B	C	E	C	B	E	E	B	C	E	C	B

Note: B: Base  
 C: Collector  
 E: Emitter